



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of )

Hisao HAYASHI et al )

Appln. No. 09/772,986 ✓ )

Filed: January 31, 2001 )

For: THIN FILM SEMICONDUCTOR )  
 DEVICE, DISPLAY DEVICE USING )  
 SUCH THIN FILM SEMI- )  
 CONDUCTOR DEVICE AND )  
 MANUFACTURING METHOD )  
 THEREOF )

Group Art Unit: 2811

Examiner: Tran, Thien F.

*Suppl.  
Response  
#10  
Wheeler  
9.13.02*

**BOX NON-FEE AMENDMENT**  
**Commissioner of Patents**  
**Washington, D.C. 20231**

**SUPPLEMENTAL RESPONSE**

Sir:

In addition to the amendment and response filed on August 8, 2002, responsive to the non-final Office Action dated May 8, 2002, please consider the remarks set forth below.

**REMARKS**

Applicant now provides a full translation of the Examiner's cited reference Hisao et al (JP 10209467). Applicant requests reconsideration of the claims in view of the text of the cited reference and the following remarks.

**35 USC § 103 Rejection**

The Examiner rejects Claims 1-8 under 35 USC §103 as being unpatentable over Hisao et al (JP 10209467). The Examiner states that Hisao discloses a gate electrode having a thickness of about 100 nm which could be more or less than 100 nm. The Examiner states that because the general conditions of the claim are disclosed, it would be obvious to one of ordinary skill in the art to modify Hisao to the less than 100 nm range.

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